

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ Max}$	$I_D \text{ Max}$ $T_A = +25^\circ\text{C}$
-30V	13m $\Omega$ @ $V_{GS} = -10\text{V}$	-9.8A
	25m $\Omega$ @ $V_{GS} = -4.5\text{V}$	-7.0A

## Description

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

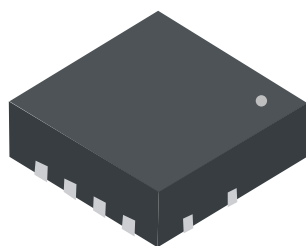
## Features and Benefits

- Low  $R_{DS(ON)}$  – Ensures On-State Losses Are Minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

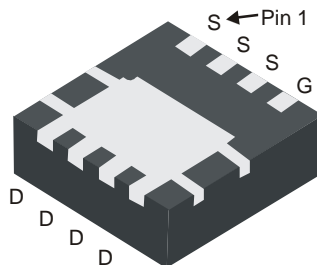
## Mechanical Data

- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.0174 grams (Approximate)

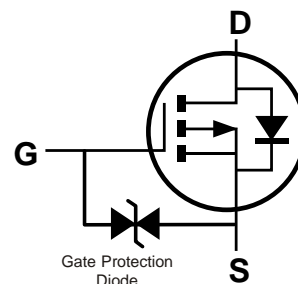
### POWERDI3333-8



Top View



Bottom View



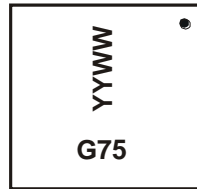
Equivalent Circuit

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMG7401SFGQ-7	POWERDI3333-8	2,000/Tape & Reel
DMG7401SFGQ-13	POWERDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_compliance\\_definitions/](http://www.diodes.com/quality/product_compliance_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



G75 = Product Marking Code  
 YYWW = Date Code Marking  
 YY = Last Digit of Year (ex: 10 for 2010)  
 WW = Week Code (01 – 53)

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-9.8 -7.7	A
	t<10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-13.5 -10.8	A
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	-3.0	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I <sub>DM</sub>	-80	A
Avalanche Current (Notes 8 & 9)			I <sub>AR</sub>	14	A
Repetitive Avalanche Energy (Notes 8 & 9) L = 1mH			E <sub>AR</sub>	104	mJ

## Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.94	W
	T <sub>A</sub> = +70°C		0.6	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	137	°C/W
	t < 10s		82	
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.2	W
	T <sub>A</sub> = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R <sub>θJA</sub>	60	°C/W
	t < 10s		36	
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	3.0	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.  
 8. I<sub>AR</sub> and E<sub>AR</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.7	—	-3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	9	11	mΩ	V <sub>GS</sub> = -20V, I <sub>D</sub> = -12A
		—	10	13		V <sub>GS</sub> = -10V, I <sub>D</sub> = -9A
		—	17	25		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5A
Forward Transfer Admittance	Y <sub>fs</sub>	—	21	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -10A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C <sub>iss</sub>	—	2,246	2,987	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	352	468	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	294	391	pF	
Gate resistance	R <sub>g</sub>	—	5.1	10	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	20.5	30	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -12A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	41	58	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	7.6	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	8.0	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	11.3	23	nS	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V, R <sub>L</sub> = 1.25Ω, R <sub>G</sub> = 3Ω,
Turn-On Rise Time	t <sub>r</sub>	—	15.4	31	nS	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	38.0	61	nS	
Turn-Off Fall Time	t <sub>f</sub>	—	22.0	38	nS	
BODY DIODE CHARACTERISTICS						
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	—	20	31	nS	I <sub>S</sub> = -9.5A, dI/dt = 100A/μs
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	—	9.5	18	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.  
10. Guaranteed by design. Not subject to product testing.

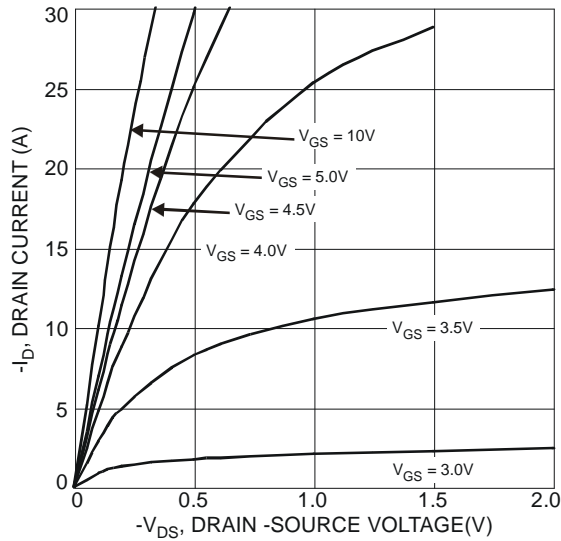


Fig. 1 Typical Output Characteristics

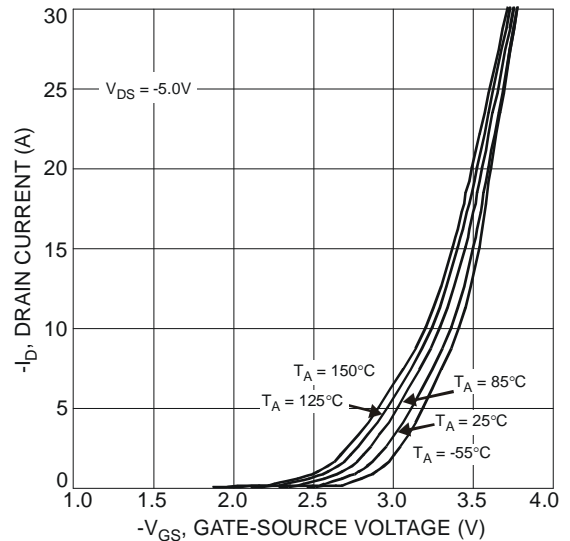


Fig. 2 Typical Transfer Characteristics

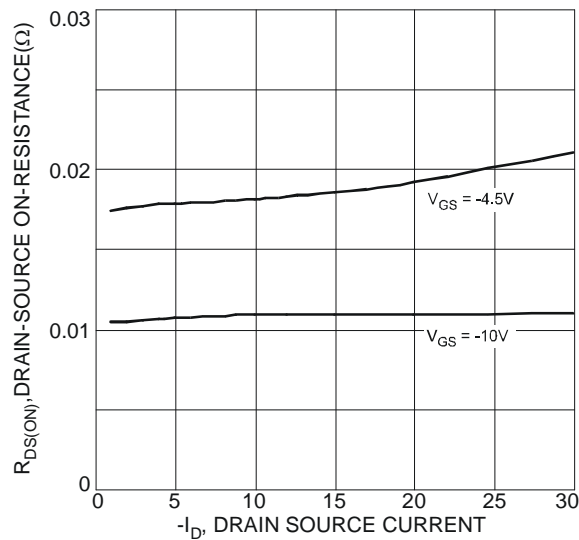


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

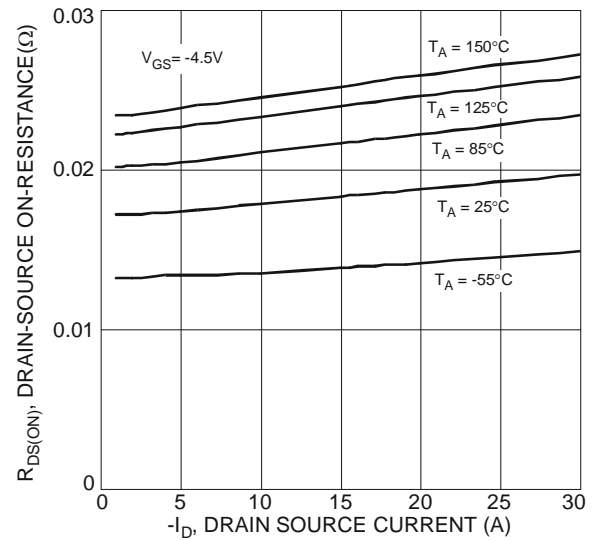


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

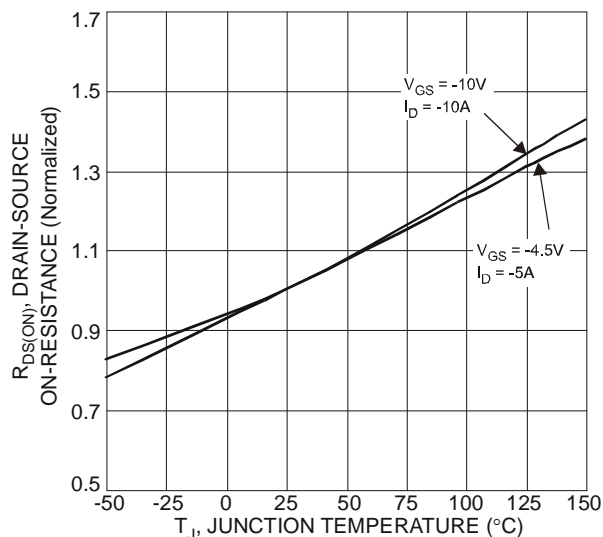


Fig. 5 On-Resistance Variation with Temperature

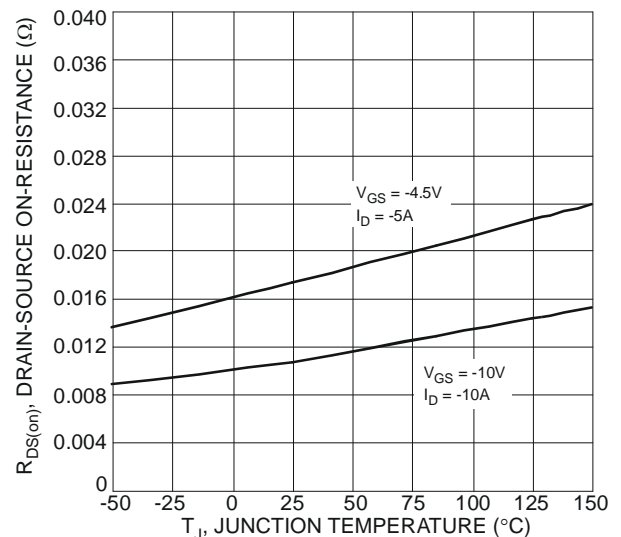


Fig. 6 On-Resistance Variation with Temperature

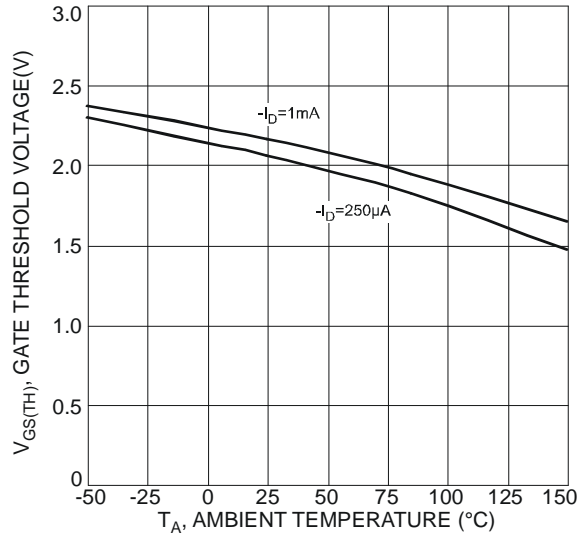


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

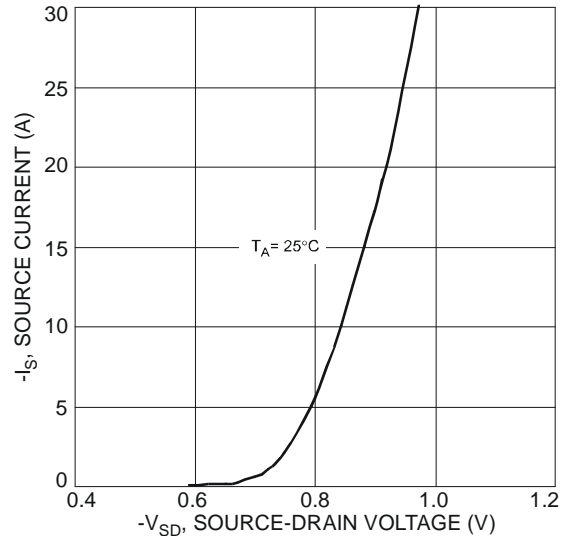


Fig. 8 Diode Forward Voltage vs. Current

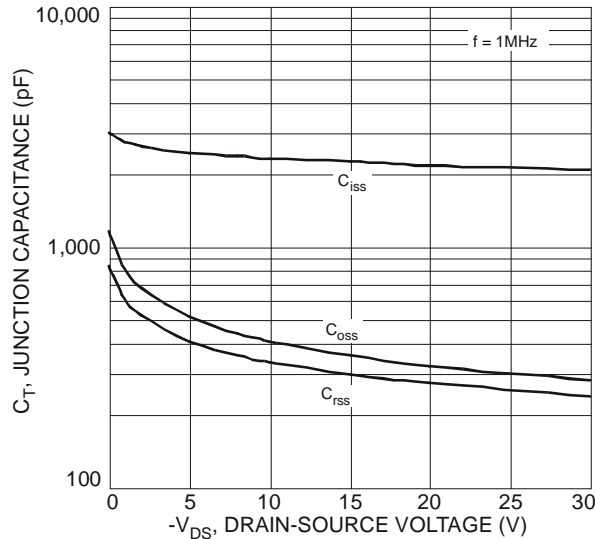


Fig. 9 Typical Junction Capacitance

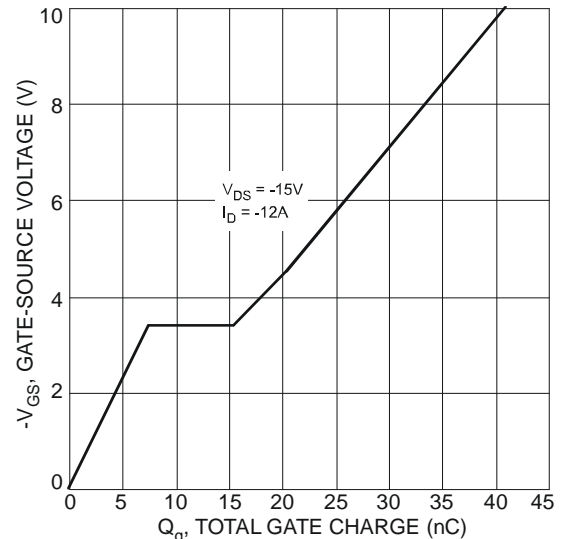


Fig. 10 Gate-Charge Characteristics

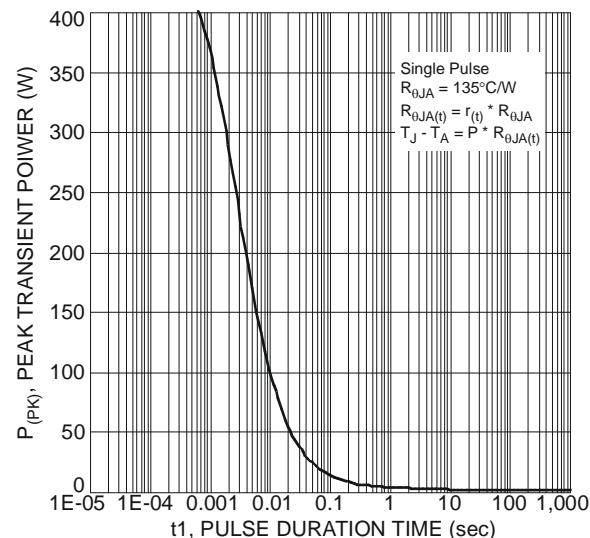


Fig. 11 Single Pulse Maximum Power Dissipation

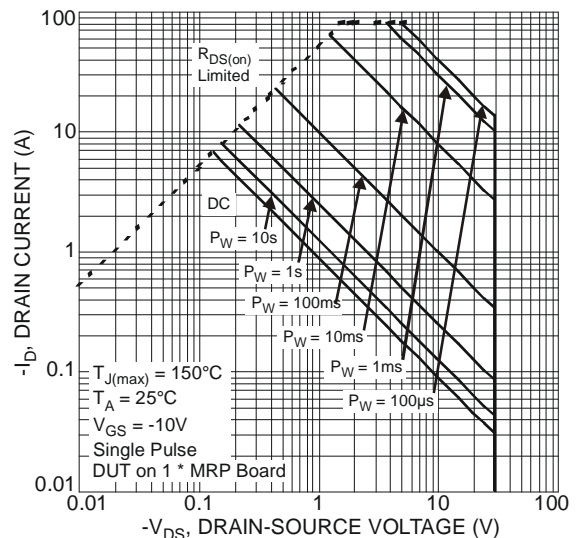
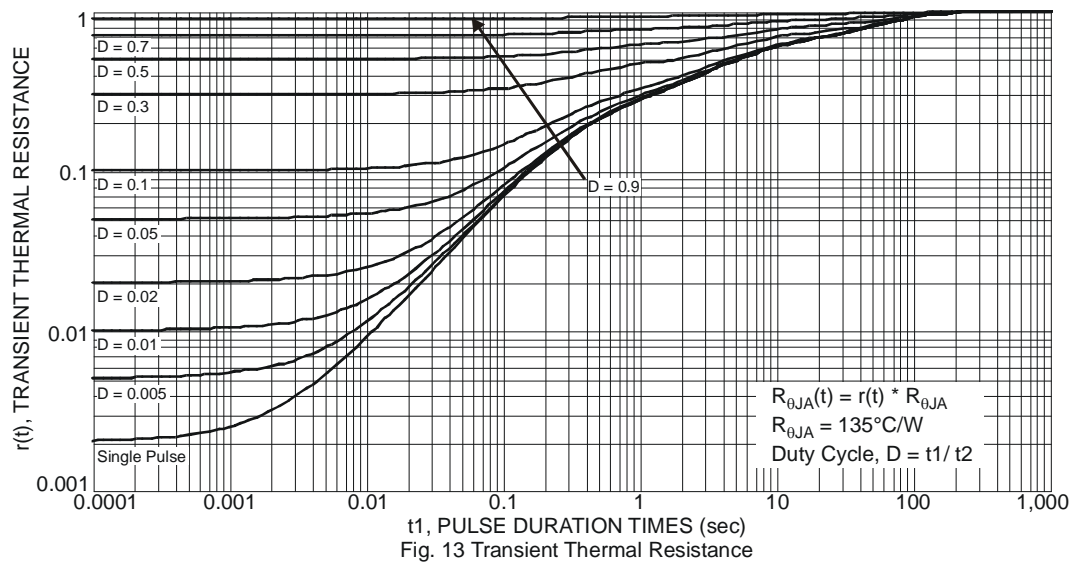


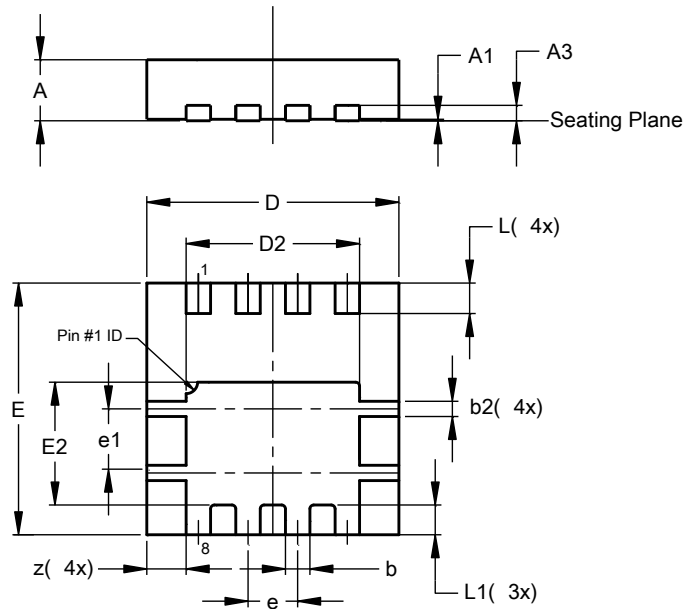
Fig. 12 SOA, Safe Operation Area



## Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

### POWERDI3333-8

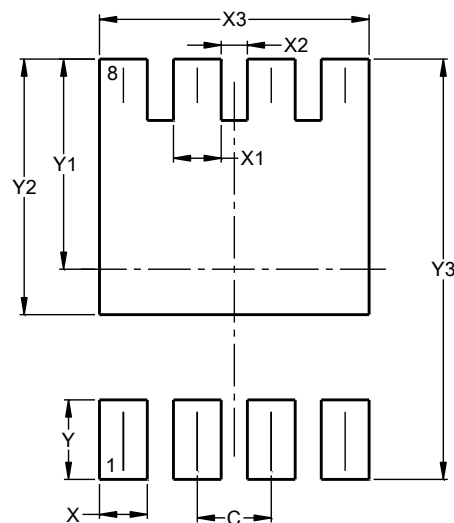


POWERDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	—	—	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	—	—	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

### POWERDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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